Paper Code: ECC-215

## END TERM EXAMINATION THIRD SEMESTER [B. TECH] DECEMBER 2024

Time: 3 Hours Subject: Electronics-I Note: Attempt all questions as directed. Internal choice is indicated. Maximum Marks: 60 Attempt any Four of the following Questions. Q1 (a) Draw the energy band for Metal, Semiconductor and Insulator. (4x5=20)(b) Write the difference between Direct band semiconductor and Indirect band (c) A diode has leakage current of 5μA at 10 °C. Find its value when the Write short notes on Zener diode and draw the V-I characteristics. (e) Draw and write the operation of npn transistor in active region. Reduce the following Boolean fiction using Boolean algebra. (g) Draw and explain the Full Adder.  $F = AB + \vec{A}B + BC$ (h) Write the difference between Synchronous Counter and Asynchronous Q2 A pure semiconductor (Ge) is doped with donor impurities to the extent of 107. (10)FindDonor concertation, Electron concentration, Hole concentration And Conductivity of the doped semiconductor. (Assume: Total number of atoms in Ge is 4.4x10<sup>23</sup> cm<sup>-3</sup>. n<sub>i</sub>=2.5x10<sup>13</sup> Atom/cm<sup>-3</sup>,  $\mu_n$ =3800 cm<sup>2</sup>/V-Sec,  $\mu_p$ =1800 cm<sup>2</sup>/V-Sec). Explain working of Tunnel diode with V-I characteristics and suitable diagrams. Q3 (10)04 Explain Half wave rectifier and full wave rectifier with suitable circuit diagram and (10)waveform. OR Explain working of Common Emitter (CE) configuration of npn transistor with Q5 (10)suitable diagrams. Also draw the input and output characteristics. Write the operation of N-Channel enhancement MOSFET and depletion MOSFET (10)Q6 with suitable block diagram and V-I characteristics. Reduce the following Boolean function using K-map. (10)**Q7**  $f(A, B, C, D) = \sum m(0, 1, 3, 5, 9, 11, 13) + \sum d(7, 10, 15)$ Draw and explain Carry Look-ahead Adder in detail. (10)Q8 What is J-K Flip-flop? What is Race around condition in J-K flip-flop and how it (10)Q9 can overcome?